

# Bias Resistor Transistor

## NPN Silicon Surface Mount Transistor with Monolithic Bias Resistor Network

**LDTC115GWT1G**

● **Applications**

Inverter, Interface, Driver

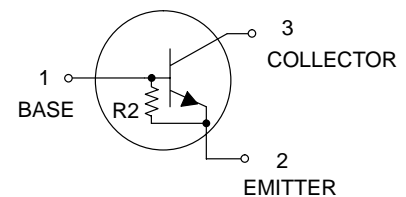
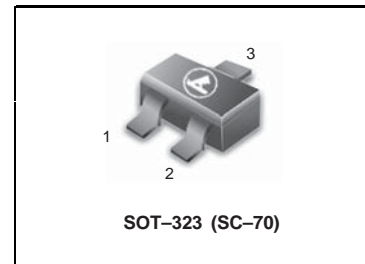
● **Features**

- 1) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit).
- 2) The bias resistors consist of thin-film resistors with complete isolation to allow positive biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.
- 3) Only the on/off conditions need to be set for operation, making the device design easy.

- We declare that the material of product compliance with RoHS requirements.

● **Absolute maximum ratings** (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V <sub>CB0</sub>	50	V
Collector-emitter voltag	V <sub>CEO</sub>	50	V
Emitter-base voltage	V <sub>EBO</sub>	5	V
Collector current	I <sub>c</sub>	100	mA
Collector power dissipation	P <sub>c</sub>	200	mW
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C



**DEVICE MARKING AND RESISTOR VALUES**

Device	Marking	R1 (K)	R2 (K)	Shipping
LDTC115GWT1G	L2	—	100	3000/Tape & Reel
LDTC115GWT3G	L2	—	100	10000/Tape & Reel

● **Electrical characteristics** (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV <sub>CB0</sub>	50	—	—	V	I <sub>c</sub> =50μA
Collector-emitter breakdown voltag	BV <sub>CEO</sub>	50	—	—	V	I <sub>c</sub> =1mA
Emitter-base breakdown voltage	BV <sub>EBO</sub>	5	—	—	V	I <sub>E</sub> =72μA
Collector cutoff current	I <sub>cBO</sub>	—	—	0.5	μA	V <sub>CB</sub> =50V
Emitter cutoff current	I <sub>EBO</sub>	30	—	58	μA	V <sub>EB</sub> =4V
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	—	—	0.3	V	I <sub>c</sub> =5mA, I <sub>B</sub> =0.25mA
DC current transfer ratio	h <sub>FE</sub>	82	—	—	—	I <sub>c</sub> =5mA, V <sub>CE</sub> =5V
Emitter-base resistance	R	70	100	130	kΩ	—
Transition frequency	f <sub>r</sub> *	—	250	—	MHz	V <sub>CE</sub> =10V, I <sub>E</sub> =-5mA, f=100MHz

\* Characteristics of built-in transistor

**LDTC115GWT1G**

● **Electrical characteristic curves**

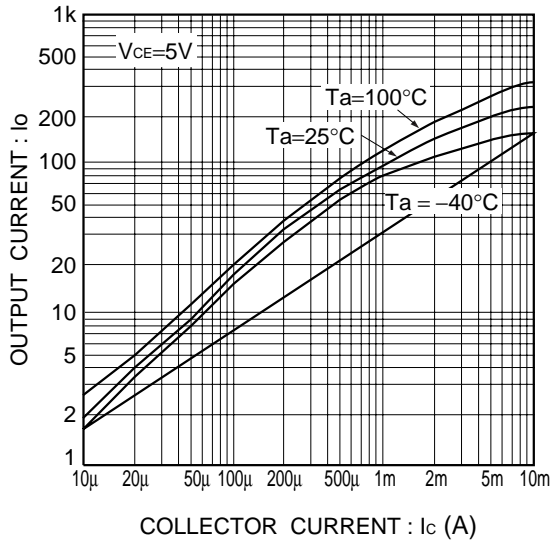


Fig.1 DC current transfer ratio vs. collector current characteristics

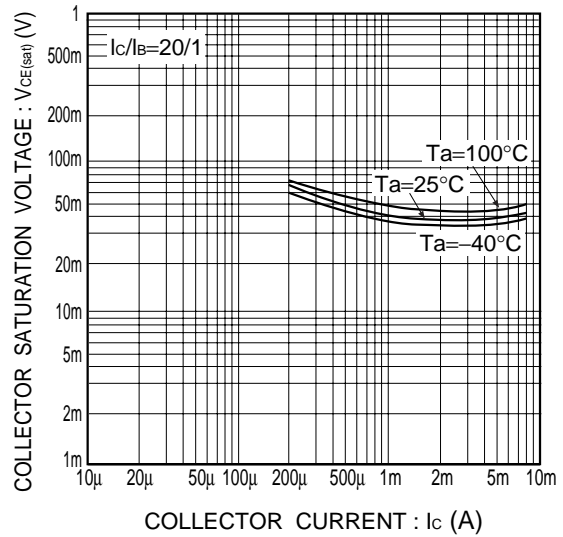
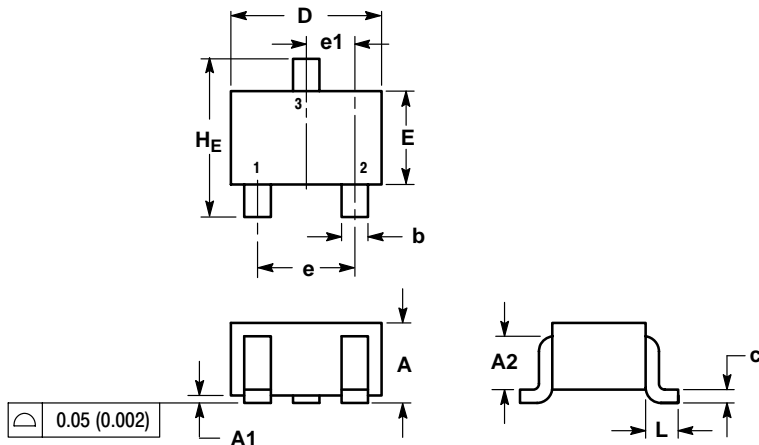


Fig.2 Collector-emitter saturation voltage vs. collector current characteristics

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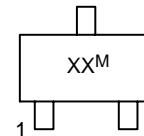
**SC-70 (SOT-323)**



NOTES:  
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.  
 2. CONTROLLING DIMENSION: INCH.

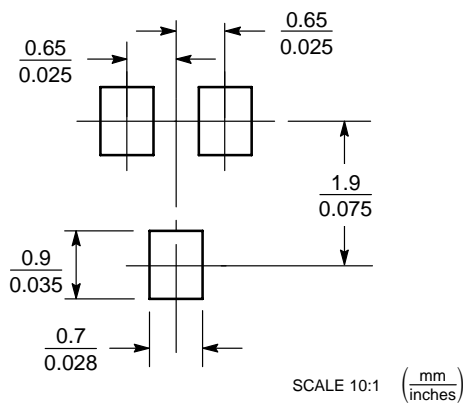
DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.7 REF			0.028 REF		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.425 REF			0.017 REF		
HE	2.00	2.10	2.40	0.079	0.083	0.095

**GENERIC MARKING DIAGRAM**



XX = Specific Device Code  
 M = Date Code  
 ■ = Pb-Free Package

**SOLDERING FOOTPRINT\***



\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present.